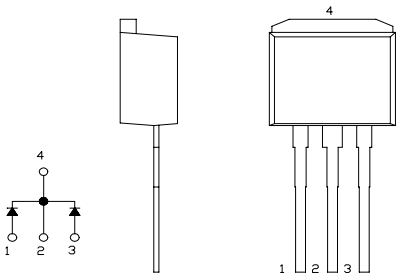


SBD T y p e : C10T10Q-11A

OUTLINE DRAWING

FEATURES

- *Tabless TO-220
- *Dual Diodes – Cathode Common
- *Low Forward Voltage Drop
- *High Surge Capability
- *Tj=150 °C operation



Maximum Ratings

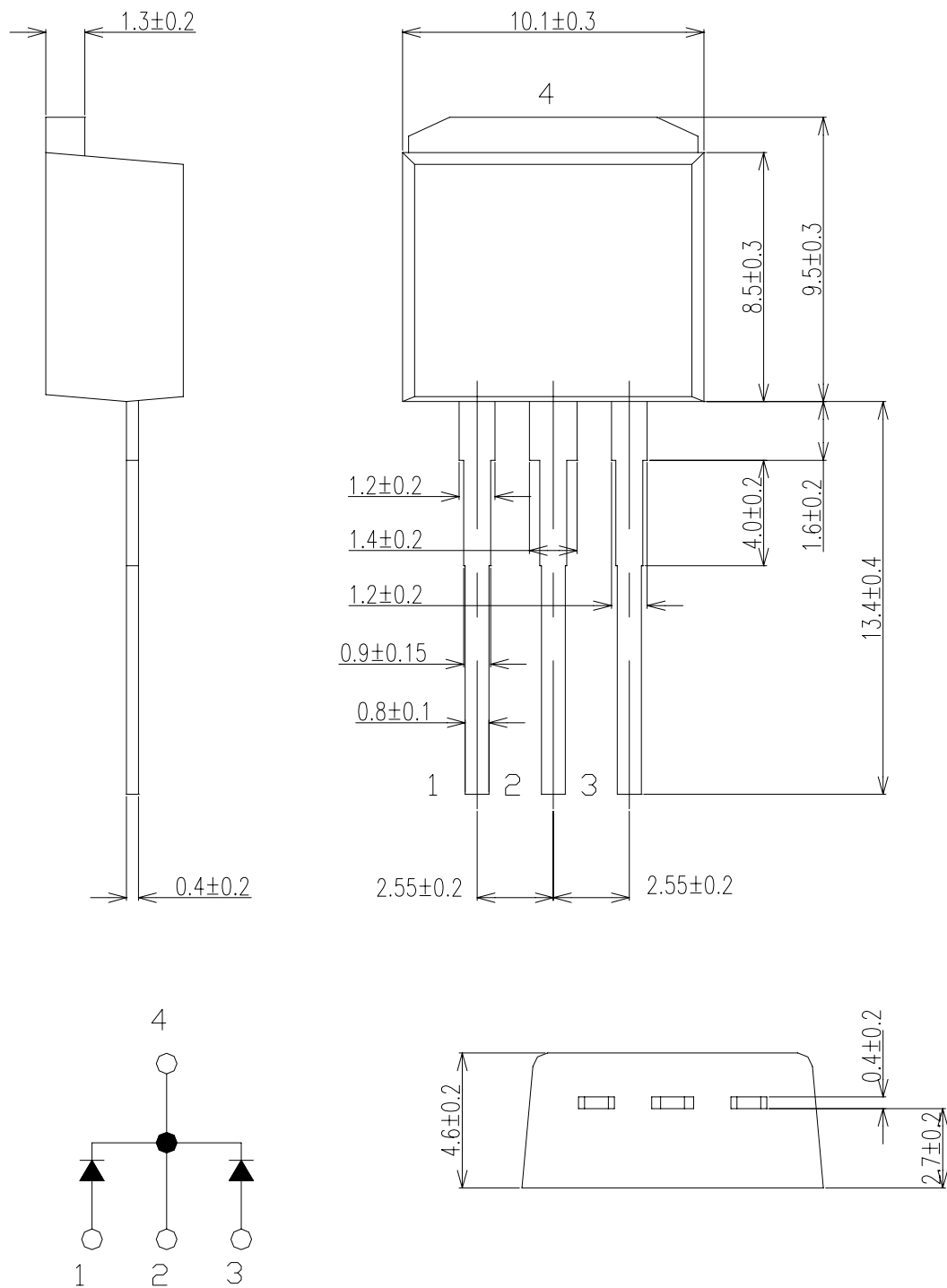
Approx Net Weight: 1.45g

Rating	Symbol	C10T10Q-11A			Unit
Repetitive Peak Reverse Voltage	V _{RRM}	100			V
Average Rectified Output Current	I _O	10	Tc=121℃	50 Hz Full Sine Wave Resistive Load	A
RMS Forward Current	I _{F(RMS)}	11.1			A
Surge Forward Current	I _{FSM}	120	50Hz Full Sine Wave ,1cycle Non-repetitive		A
Operating JunctionTemperature Range	T _{jw}	-40 to +150			℃
Storage Temperature Range	T _{stg}	-40 to +150			℃

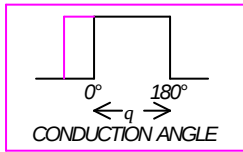
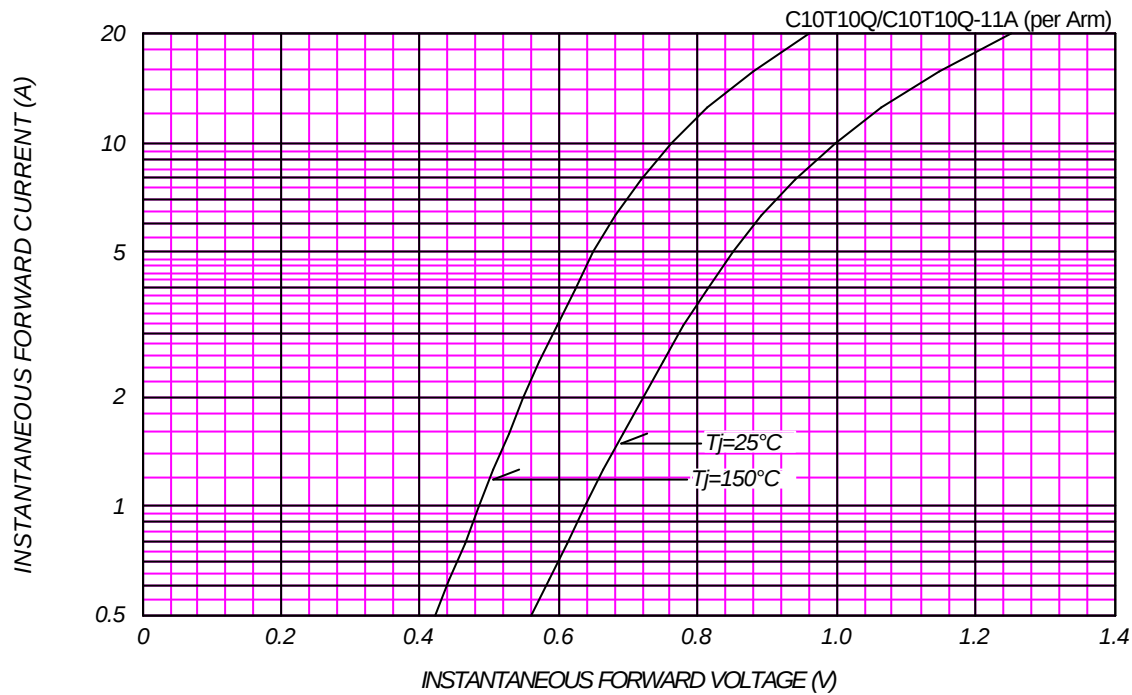
Electrical • Thermal Characteristics

Characteristics	Symbol	Conditions	Min.	Typ.	Max.	Unit
Peak Reverse Current	I _{RM}	Tj= 25°C, V _{RM} = V _{RRM} per arm	-	-	1	mA
Peak Forward Voltage	V _{FM}	Tj= 25°C, I _{FM} = 5 A per arm	-	-	0.85	V
Thermal Resistance	Rth(j-c)	Junction to Case	-	-	3	°C /W

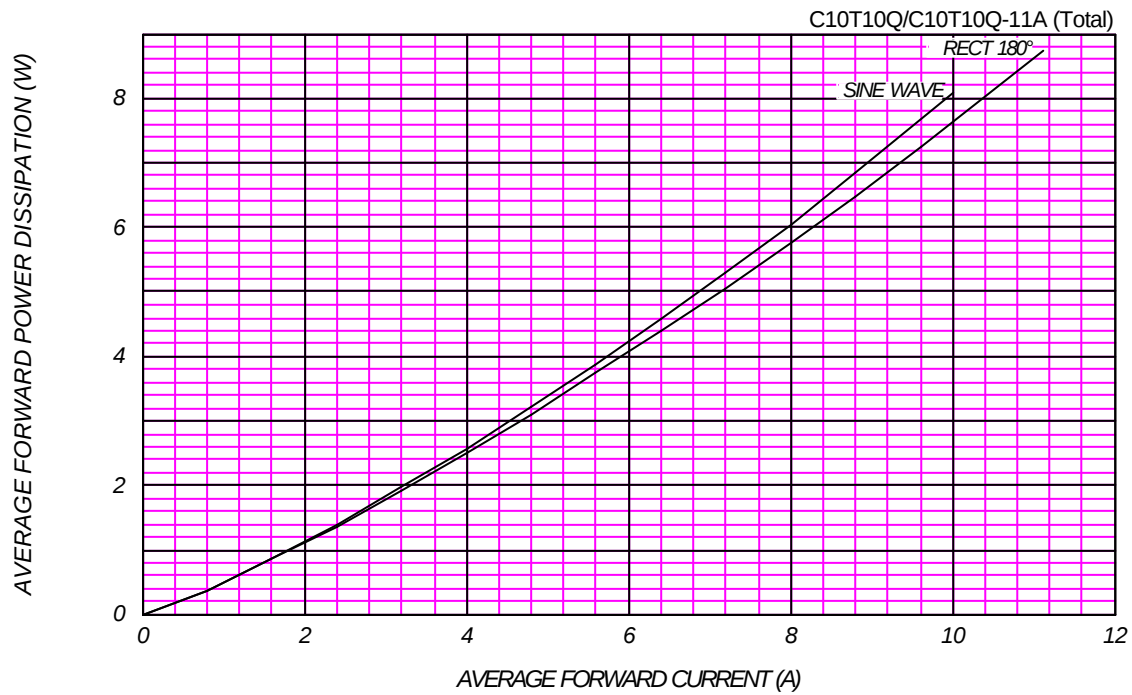
C_T_ 11A OUTLINE DRAWING (Dimensions in mm)



FORWARD CURRENT VS. VOLTAGE



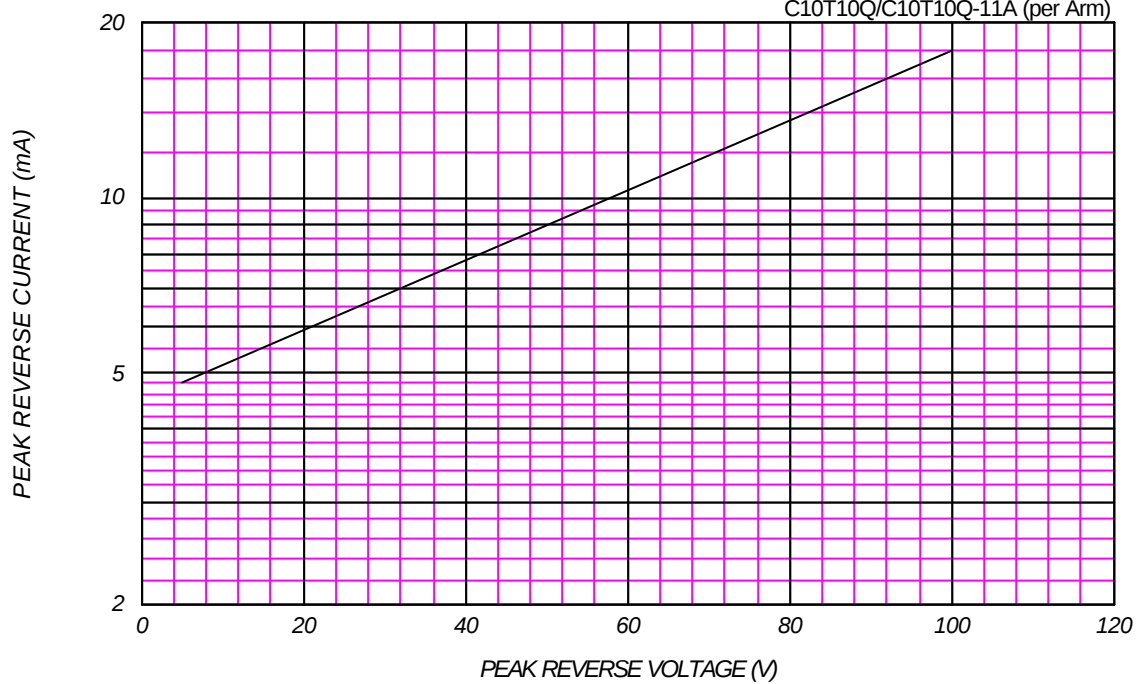
AVERAGE FORWARD POWER DISSIPATION



PEAK REVERSE CURRENT VS. PEAK REVERSE VOLTAGE

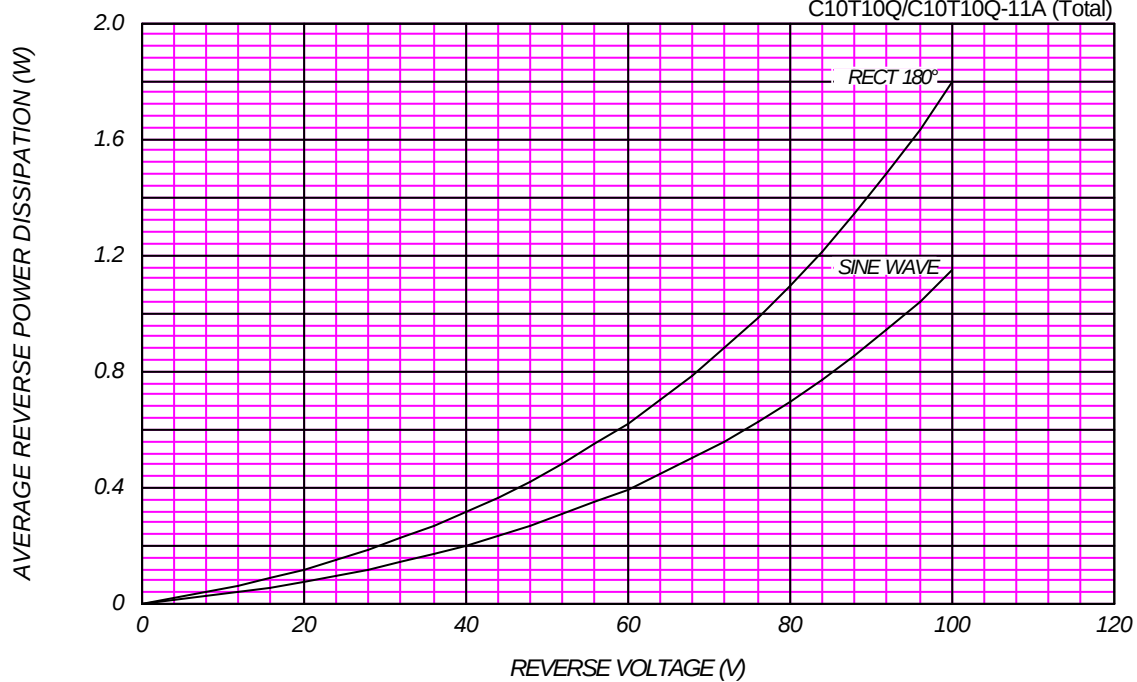
$T_j = 150^\circ\text{C}$

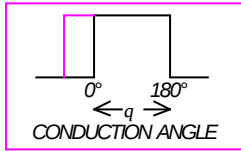
C10T10Q/C10T10Q-11A (per Arm)



AVERAGE REVERSE POWER DISSIPATION

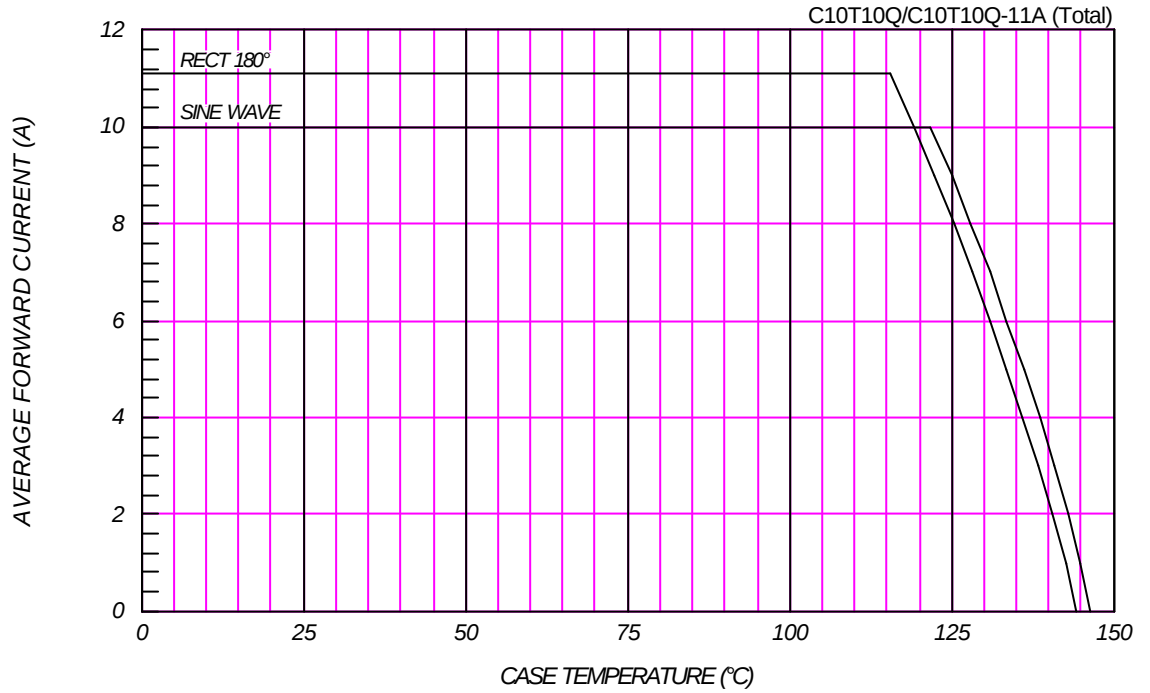
C10T10Q/C10T10Q-11A (Total)





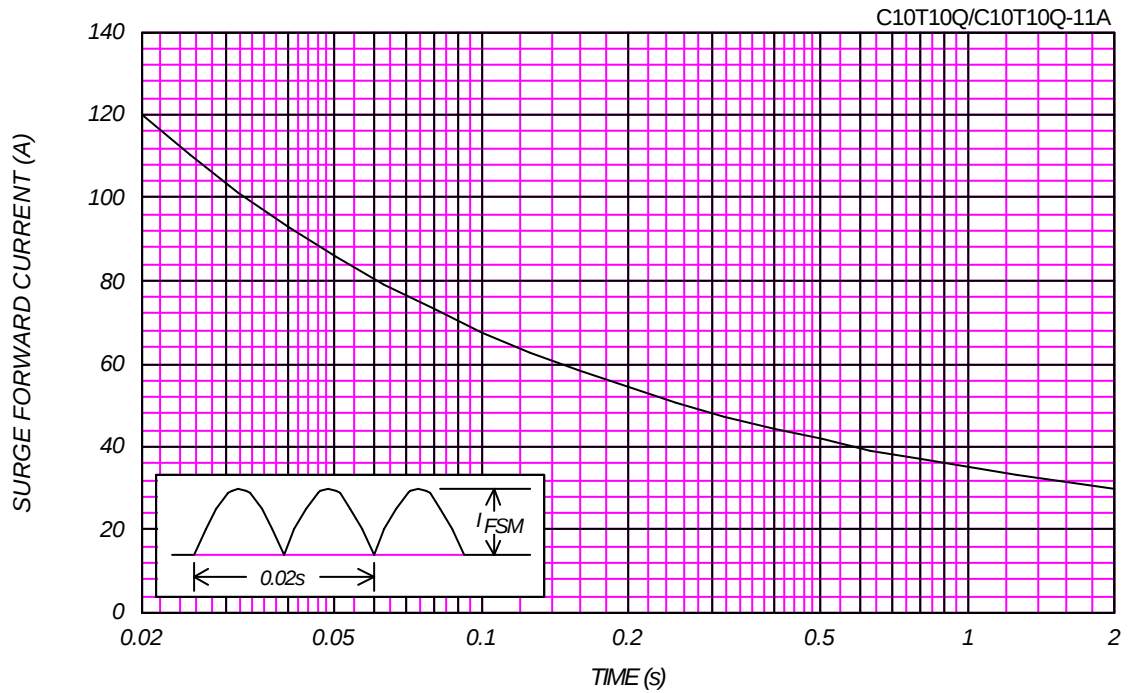
AVERAGE FORWARD CURRENT VS. CASE TEMPERATURE

$V_{RM} = 100V$



SURGE CURRENT RATINGS

$f=50Hz$, Sine Wave, Non-Repetitive, No Load



JUNCTION CAPACITANCE VS. REVERSE VOLTAGE

$T_j=25^{\circ}\text{C}$, $V_m=20\text{mV}_{\text{RMS}}$, $f=100\text{kHz}$, Typical Value

C10T10Q/C10T10Q-11A (per Arm)

